



10191/1629]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor : Franz LAERMER et al.
Serial Number : 09/720,761
Filing Date : March 26, 2001
For : METHOD OF PLASMA ETCHING OF SILICON
Examiner : Kin Chan Chen
Art Group : 1765

Commissioner for Patents
Washington, D.C. 20231

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Date: February 6, 2003

Signature: 
R. No. 36197

AMENDMENT TRANSMITTAL

SIR:

Transmitted herewith is an Amendment in response to the Office Action mailed November 6, 2002 for the above-identified application.

If any fees are due please charge the deposit account of **Kenyon & Kenyon**, number 11-0600.

Respectfully submitted,


Richard L. Mayer
Reg. No. 22,490



26646

PATENT TRADEMARK OFFICE

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Washington, D.C. 20231

Date: 2/6/03 Reg. No. 22.490

Signature: Richard L. Mayer (69, 1st
Richard L. Mayer
76, 197)

AMENDMENT

SIR:

In response to the Office Action of November 6, 2002, please amend the above-captioned application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning on page 3, line 32 with the following paragraph:

--NF₃, an additive used from time to time in the process gas to consume the passivating material, in particular SiO₂ or a teflon-type material, has the advantage over additives based on fluorocarbon compounds known from the related art that considerably stronger stripping of the dielectric layers masking the structure base is achieved, so that it has to be used in considerably smaller amounts in the respective plasma etching process compared to the known additives, with the result that the overall process is less subject to negative effects, in particular dilution of the other active reagents, which otherwise necessarily occurs. The additive may also include a fluoroalkane.--.